ABSTRACT

This disclosure provides a method and device for detecting a silicon wafer edge defect, a processing method and a product. The method includes: after a polishing process, detecting an edge of the silicon wafer by using a laser beam generated by an optical detection device to determine at least one target region which is identified as an abnormality; determining at least one delocalization value of the target region based on a laser beam feedback signal strength at the target region, each delocalization value being a difference between the feedback signal strengths at a position and its adjacent position, and an angle of circumference of the silicon wafer corresponding to the position and an angle of circumference corresponding to the adjacent position differ by a predetermined angle; and when the delocalization value of the target region meets a predetermined condition, determining that the target region is an edge haze defect.

(Figure 6)